

# TESDF5V0A Bi-Directional ESD Protection Array

### **Small Signal Diode**



#### Features

- ♦Meet IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- Meet IEC61000-4-5 (Lightning) rating. 12A (8/20µs)
- ♦Protects two directional I/O lines
- ♦Working Voltage : 5V
- ♦Pb free version, RoHS compliant, and Halogen free

#### **Mechanical Data**

- ♦Case :SOT-23 standard package, molded plastic
- Terminal: Matte tin plated, lead free., solderable per MIL-STD-202, Method 202 guaranteed
- ♦High temperature soldering guaranteed: 260°C/10s
- ♦Weight : 0.008gram (approximately)
- ♦Marking Code : L50

### **Applications**

- ♦Cell Phone Handsets and Accessories
- Microprocessor based equipment
- ♦Industrial Controls
- Notebooks, Desktops, and Servers



#### **Ordering Information**

| Part No.  | Package | Packing      | Packing Code | Marking |
|-----------|---------|--------------|--------------|---------|
| TESDF5V0A | SOT-23  | 3K / 7" Reel | RFG          | L50     |

### **Maximum Ratings and Electrical Characteristics**

Rating at 25°C ambient temperature unless otherwise specified.

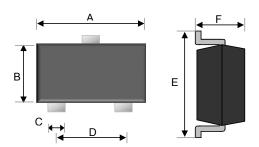
#### **Maximum Ratings**

| Type Number  | Symbol   | Value        | Units |
|--|----------|--------------|-------|
| Peak Pulse Power (tp=8/20µs waveform)                          | Ppp      | 100          | W     |
| Peak Pulse Current (tp = 8/20µs)                               | IPP      | 2.5          | А     |
| ESD per IEC 61000-4-2 (Air)<br>ESD per IEC 61000-4-2 (Contact) | VESD     | ±15<br>± 8   | KV    |
| Junction and Storage Temperature Range                         | Tj, Tstg | -55 to + 150 | °C    |

#### **Electrical Characteristics**

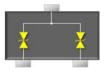
| Type Number               |                              | Symbol            | Min  | Max   | Units |
|---------------------------|------------------------------|-------------------|------|-------|-------|
| Reverse Stand-Off Voltage |                              | VRWM              | -    | 5     | V     |
| Reverse Breakdown Voltag  | l <sub>R</sub> = 1mA         | V <sub>(BR)</sub> | 6    | -     | V     |
| Reverse Leakage Current   | V <sub>R</sub> = 5V          | IR                | -    | 1     | uA    |
| Clamping Voltage          | I <sub>PP</sub> = 1A         | Vc                | -    | 9.8   | V     |
|                           | I <sub>PP</sub> = 2.5A       |                   | -    | 15    |       |
| Junction Capacitance      | V <sub>R</sub> =0V, f=1.0MHz | CJ                | 10 ( | Тур.) | pF    |





| Dimensions | Unit (mm) |      | Unit (inch) |       |
|------------|-----------|------|-------------|-------|
| Dimensions | Min       | Max  | Min         | Max   |
| A          | 2.80      | 3.00 | 0.110       | 0.118 |
| В          | 1.20      | 1.40 | 0.047       | 0.055 |
| С          | 0.30      | 0.50 | 0.012       | 0.020 |
| D          | 1.80      | 2.00 | 0.071       | 0.079 |
| E          | 2.25      | 2.55 | 0.089       | 0.100 |
| F          | 0.90      | 1.20 | 0.035       | 0.043 |

# **Pin Configutation**





## **Small Signal Diode**

## **Rating and Characteristic Curves**

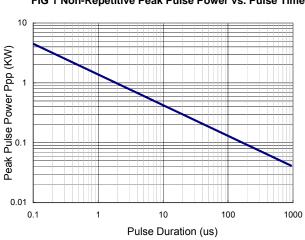
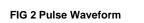
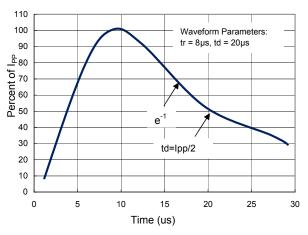
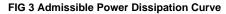


FIG 1 Non-Repetitive Peak Pulse Power vs. Pulse Time







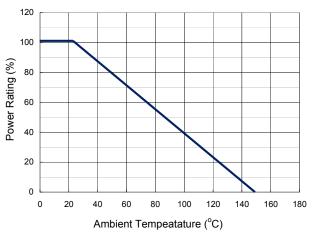


FIG 5 Clamping Voltage vs. Peak Pulse Current

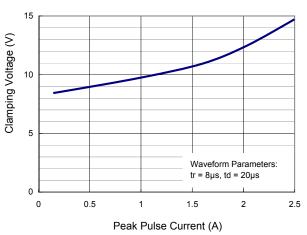
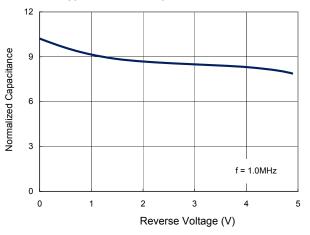


FIG 4 Typical Junction Capacitance





# TESDF5V0A Bi-Directional ESD Protection Array

# Small Signal Diode

# **Applications Information**

♦Designed for the bi-directional protection of 2 lines from the damage caused by Electro Static Discharge (ESD) and surge pulses

 $\diamond \mathsf{Be}$  used on lines where the signal polarities are above and below ground

 $\diamond \mathsf{Provides}$  a surge capability of 100 Watts peak Ppp per line for an 8/20 ms waveform.

# **Circuit Board Layout Recommendations**

 $\diamond \mathsf{P}\mathsf{lace}$  the ESD protection array as close to the input terminal or connector as possible

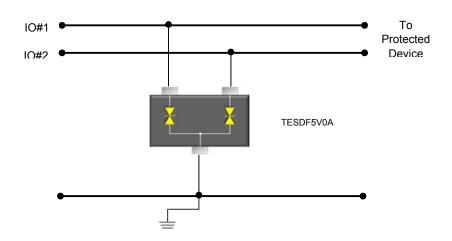
♦Keep parallel signal paths to a minimum

Minimize all printed-circuit board conductive loops including power and group loops

 $\diamond$ Avoid using shared transient return paths to a common ground point

 $\diamond \textsc{Ground}$  planes should be used. For multilayer printed-circuit boards, use ground vias

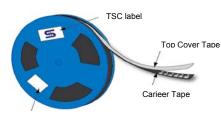
 $\diamond \mathsf{Below}$  picture is the typical application for bi-directional protection of two lines



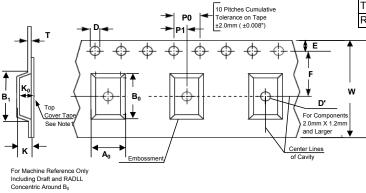


### **Small Signal Diode**

### **Tape & Reel specification**



Any Additional Label (If Required)

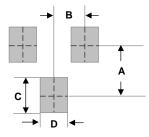


| Item                   | Symbol | Dimension (mm) |
|------------------------|--------|----------------|
| Carrier depth          | К      | 1.22 Max.      |
| Sprocket hole          | D      | 1.50 +0.10     |
| Reel outside diameter  | А      | 180 ± 1        |
| Reel inner diameter    | D1     | 50 Min.        |
| Feed hole width        | D2     | 13.0 ± 0.5     |
| Sprocke hole position  | E      | 1.75 ±0.10     |
| Sprocke hole pitch     | P0     | 4.00 ±0.10     |
| Embossment center      | P1     | 2.00 ±0.10     |
| Overall tape thickness | Т      | 0.6 Max.       |
| Tape width             | W      | 8.30 Max.      |
| Reel width             | W1     | 14.4 Max.      |



Direction of Feed

### Suggested PAD Layout



| Dimensions | Unit (inch) | Unit (mm) |
|------------|-------------|-----------|
| A          | 0.079       | 2.00      |
| В          | 0.037       | 0.95      |
| С          | 0.035       | 0.90      |
| D          | 0.031       | 0.80      |

Note 1:  $A_0$ ,  $B_0$ , and  $K_0$  are determined by component size. The clearance between the components and the cavity must be

within 0.05 mm min. to 0.5 mm max. The component cannot rote more than 10 ° within the determined cavity.

Note 2: If B<sub>1</sub> exceeds 4.2 mm(0.165") for 8 mm embossed tape, the tape may not feed through all tape feeders. Note 3: The suggested land pattern dimensions have been provided for reference only, as actual pad layouts

may vary despending on application.